FORWARD INTERNATIONAL ELECTRONICS LTD.

SEMICONDUCTOR
TECHNICAL DATA

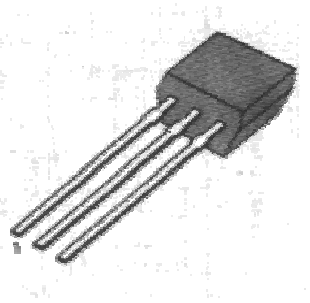
2SA1267

PNP EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY AMPLIFIER

* Complement to 2SC3199
* Collector-Emitter Voltage V_{CEO}=-50V

Package: TO-92S



PIN: / STYLE	1	2	3
NO.1	E	C	B

ABSOLUTE MAXIMUM RATINGS at Tamb=25^{0}C

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	-50	V
Collector-Emitter Voltage	Vceo	-50	V
Emitter-Base Voltage	Vebo	-5	V
Collector Current	Ic	-150	mA
Collector Dissipation	Pc	450	mW
Junction Temperature	Tj	150	^{0}C
Storage Temperature	Tstg	-55~150	^{0}C

ELECTRICAL CHARACTERISTICS at Tamb=25^{0}C

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BVcbo	-50			V	Ic=-100uA Ie=0
Collector-Emitter Breakdown Voltage	BVceo	-50			V	Ic=-1mA Ib=0
Emitter-Base Breakdown Voltage	BVebo	-5			V	Ie=-100uA Ic=0
Collector Cutoff Current	Icbo			-100	nA	Vcb=-50V Ie=0
DC Current Gain	Hfe	70		400		Vce=-6V Ic=-2mA
Collector-Emitter Saturation Voltage	Vce(sat)			-0.3	V	Ic=-100mA Ib=-10mA
Output Capacitance	Cob			7	pF	Vcb=-10V Ie=0 f=1MHz
Current Gain-Bandwidth Product	fT	80			MHz	Vce=-10V Ic=-1mA

CLASSIFICATION HFE

Classification	O	Y	GR
Hfe	70-140	120-240	200-400